TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π-MOSIII)

2SK2718

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

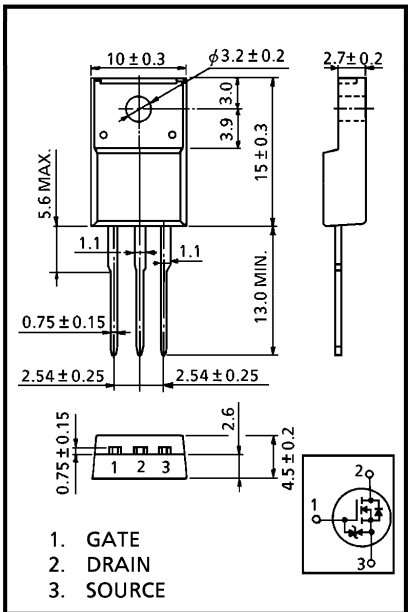
INDUSTRIAL APPLICATIONS

- Low Drain-Source ON Resistance : $R_{DS\ (ON)} = 5.6\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 2.0S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 720V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$ ($V_{DS} = 10V$, $I_D = 1mA$)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	900	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	DC	I_D	2.5	A
	Pulse	I_{DP}	7.5	A
Drain Power Dissipation (Tc = 25°C)		P_D	40	W
Single Pulse Avalanche Energy**		E_{AS}	216	mJ
Avalanche Current		I_{AR}	2.5	A
Repetitive Avalanche Energy*		E_{AR}	4.0	mJ
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

Unit in mm



JEDEC	—
EIAJ	SC-67
TOSHIBA	2-10R1B

Weight : 1.9g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th\ (ch-c)}$	3.125	°C / W
Thermal Resistance, Channel to Ambient	$R_{th\ (ch-a)}$	62.5	°C / W

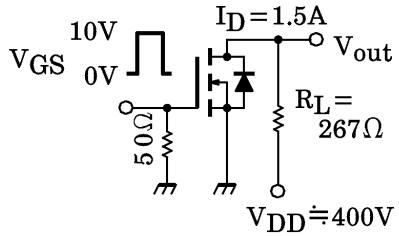
Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 90V$, Starting $T_{ch} = 25°C$, $L = 63.4mH$
$R_G = 25\Omega$, $I_{AR} = 2.5A$ (See Figure)

This transistor is an electrostatic sensitive device.
Please handle with caution.

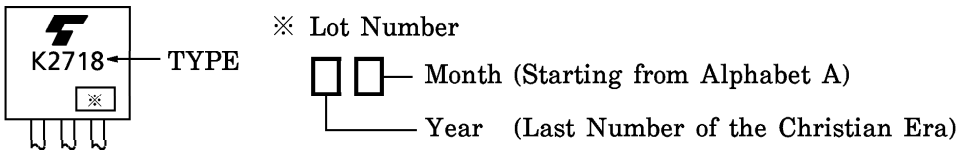
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS}=\pm25V$, $V_{DS}=0V$	—	—	±10	μA
Gate-Source Breakdown Voltage		$V_{(BR)\,GSS}$	$I_G=10\mu A$, $V_{DS}=0V$	±30	—	—	V
Drain Cut-off Current		I_{DSS}	$V_{DS}=720V$, $V_{GS}=0V$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR)\,DSS}$	$I_D=10mA$, $V_{GS}=0V$	900	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS}=10V$, $I_D=1mA$	2.0	—	4.0	V
Drain-Source ON Resistance		$R_{DS\,(ON)}$	$V_{GS}=10V$, $I_D=1.5A$	—	5.6	6.4	Ω
Forward Transfer Admittance		$\|Y_{fs}\|$	$V_{DS}=20V$, $I_D=1.5A$	1.0	2.0	—	S
Input Capacitance		C_{iss}	$V_{DS}=25V$, $V_{GS}=0V$ f = 1MHz	—	510	—	pF
Reverse Transfer Capacitance		C_{rss}		—	10	—	
Output Capacitance		C_{oss}		—	55	—	
Switching Time	Rise Time	t_r	 V_{IN} : t_r, $t_f<5ns$ Duty ≦ 1%, $t_w=10\mu s$	—	20	—	ns
	Turn-on Time	t_{on}		—	60	—	
	Fall Time	t_f		—	40	—	
	Turn-off Time	t_{off}		—	115	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD}\fallingdotseq400V$, $V_{GS}=10V$, $I_D=2.5A$	—	21	—	nC
Gate-Source Charge		Q_{gs}		—	11	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	10	—	

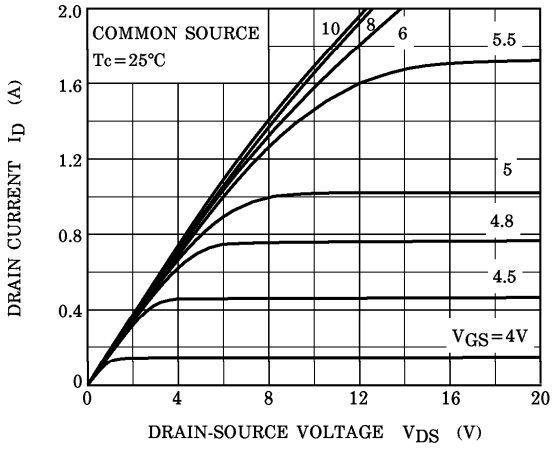
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	2.5	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	7.5	A
Diode Forward Voltage	V_{DSF}	$I_{DR}=2.5A$, $V_{GS}=0V$	—	—	−2.0	V
Reverse Recovery Time	t_{rr}	$I_{DR}=2.5A$, $V_{GS}=0V$ $dI_{DR}/dt=100A/\mu s$	—	960	—	ns
Reverse Recovery Charge	Q_{rr}		—	5.3	—	μC

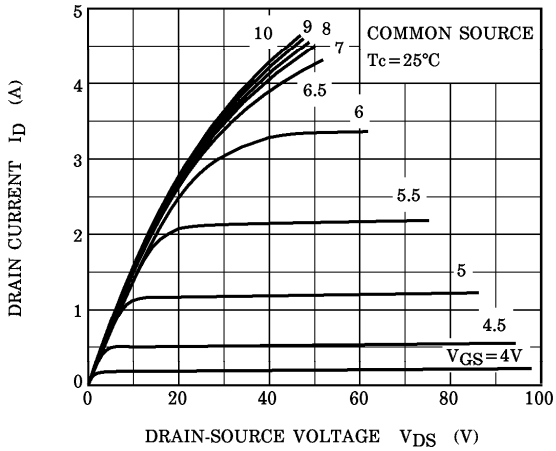
MARKING



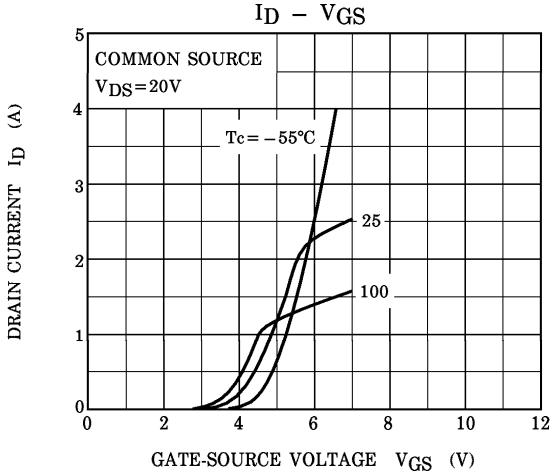
$I_D - V_{DS}$



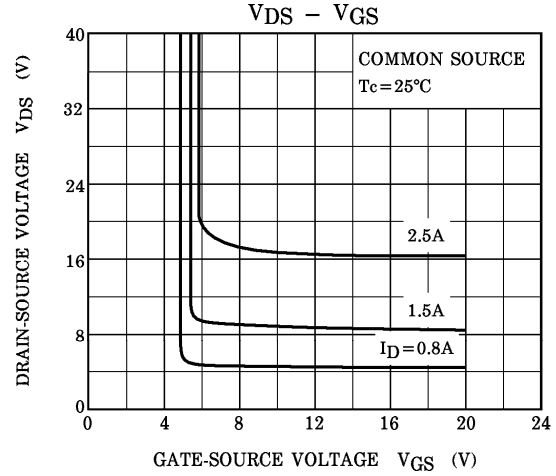
$I_D - V_{DS}$



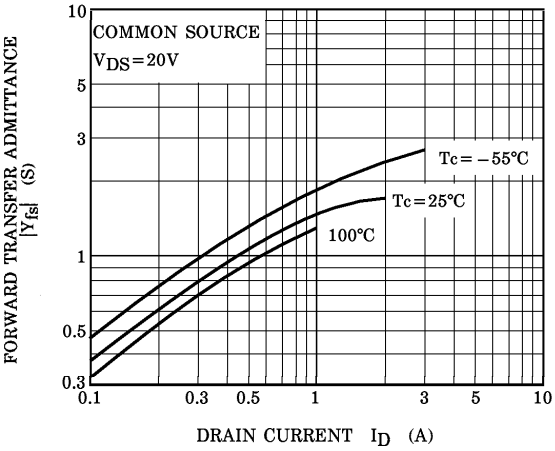
$I_D - V_{GS}$



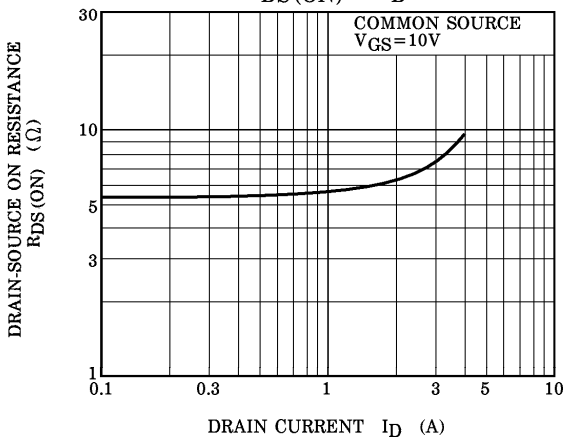
$V_{DS} - V_{GS}$



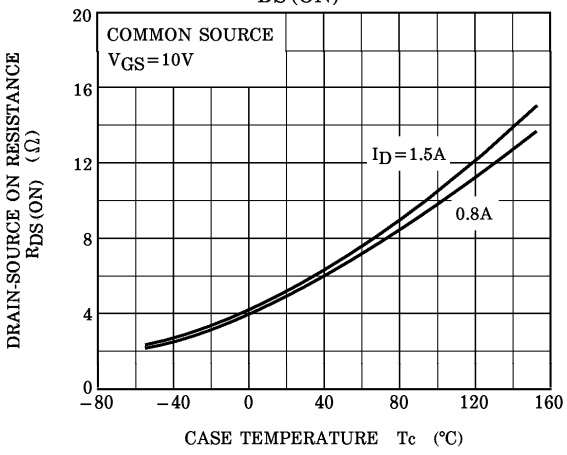
$|Y_{fs}| - I_D$



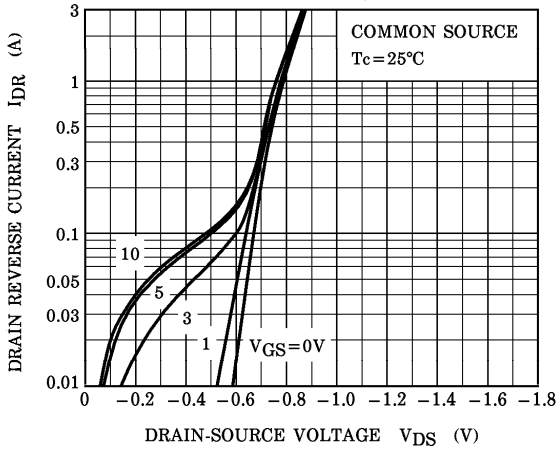
$R_{DS(ON)} - I_D$



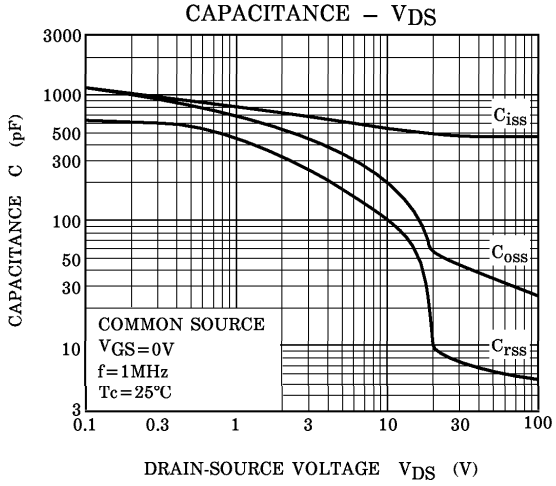
$R_{DS\,(ON)}$ – Tc



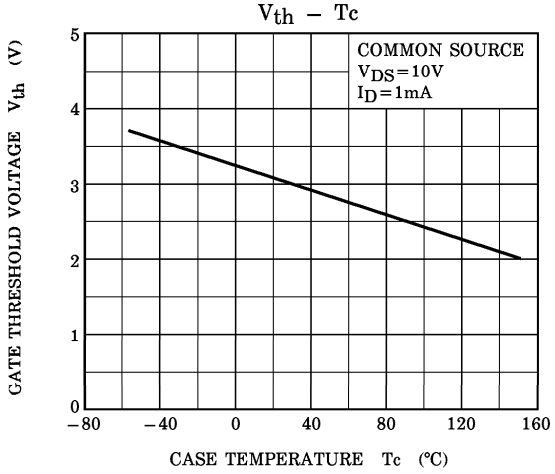
I_{DR} – V_{DS}



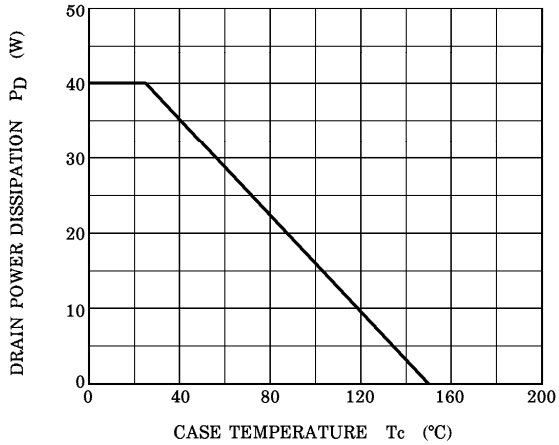
CAPACITANCE – V_{DS}



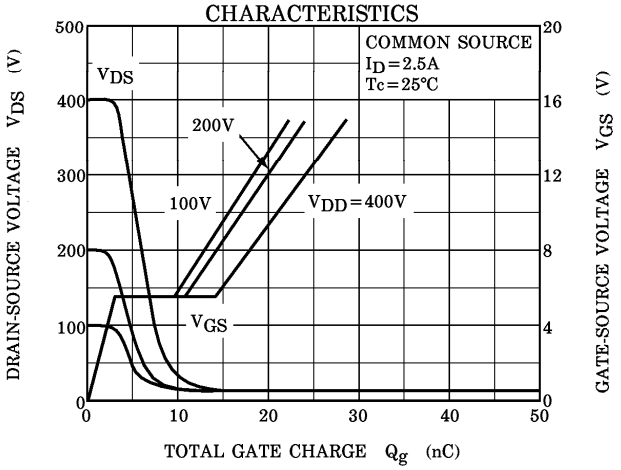
V_{th} – Tc



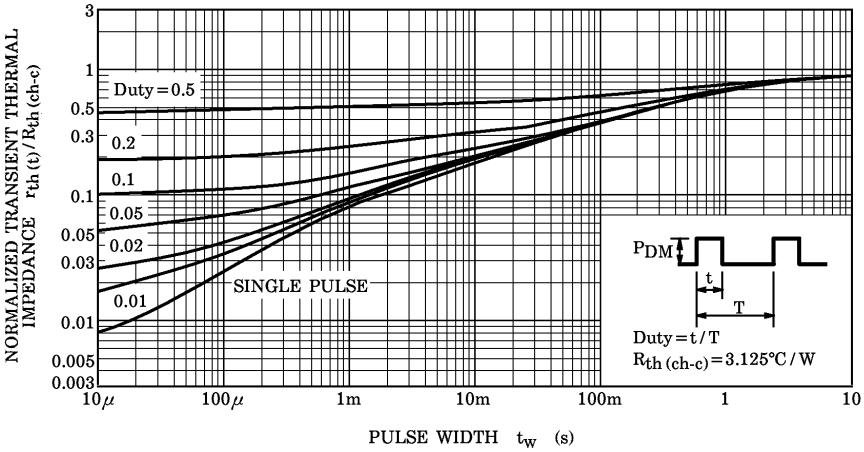
P_D – Tc



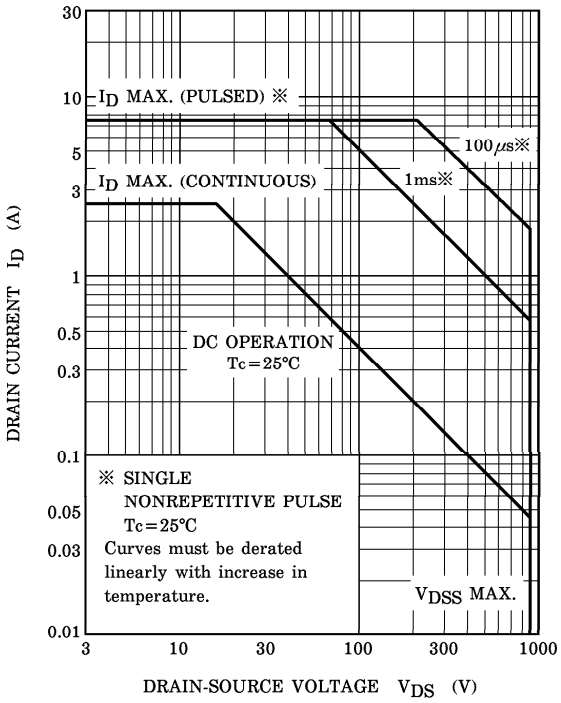
DYNAMIC INPUT / OUTPUT CHARACTERISTICS



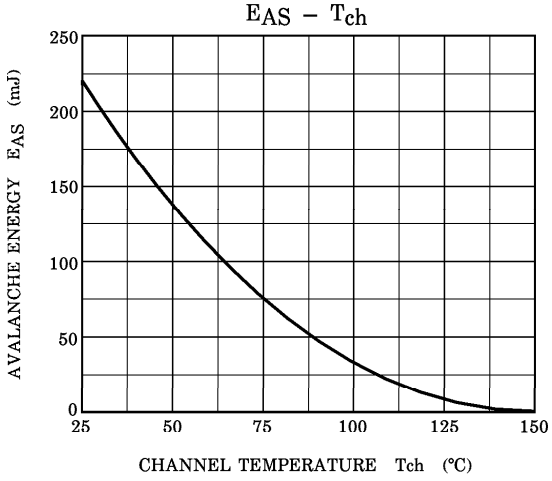
r_{th} – t_w

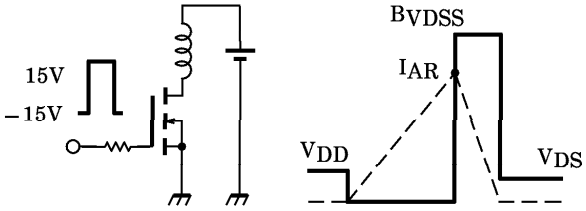


SAFE OPERATING AREA



E_{AS} – T_{ch}





TEST CIRCUIT WAVE FORM

Peak I_{AR} = 2.5A, R_G = 25Ω
V_{DD} = 90V, L = 63.4mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$